
2SD1472

Silicon NPN Epitaxial, Darlington

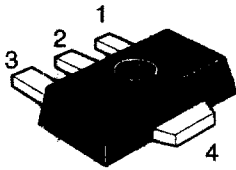
HITACHI

Application

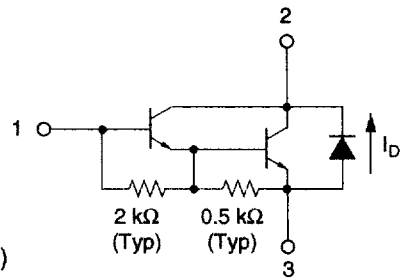
Low frequency power amplifier

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V_{CEO}	120	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	1.5	A
Collector peak current	$I_{C(\text{peak})}^{*1}$	3.0	A
Collector power dissipation	P_C^{*2}	1.0	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
E to C diode forward current	I_D	1.5	A

Notes: 1. Pluse ≤ 10 ms, Duty cycle $\leq 20\%$

2. Value on the alumina ceramic board (12.5 x 30 x 0.7 mm)

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	—	—	V	$I_C = 0.1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 10 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μA	$V_{CB} = 100 \text{ V}, I_E = 0$
	I_{CEO}	—	—	10	μA	$V_{CE} = 100 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h_{FE}	2000	—	30000		$V_{CE} = 3 \text{ V}, I_C = 1 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})1}$	—	—	1.5	V	$I_C = 1 \text{ A}, I_E = 1 \text{ mA}^{*1}$
	$V_{CE(\text{sat})2}$	—	—	2.0	V	$I_C = 1.5 \text{ A}, I_B = 1.5 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(\text{sat})1}$	—	—	2.0	V	$I_C = 1 \text{ A}, I_E = 1 \text{ mA}^{*1}$
	$V_{BE(\text{sat})2}$	—	—	2.5	V	$I_C = 1.5 \text{ A}, I_B = 1.5 \text{ mA}^{*1}$
E to C diode forward voltage	V_D	—	—	3.0	V	$I_D = 1.5 \text{ A}^{*1}$

Notes: 1. Pulse test

2. Marking is "CT".

